Supertex inc.

TN5325
Low Threshold

N-Channel Enhancement-Mode Vertical DMOS FETs

Ordering Information

BV_{DSS} / BV_{DGS}	$R_{DS(ON)}$ (max)	$V_{GS(th)}$ (max)	$I_{D(on)}$ (min)	Order Number / Package		
				TO-236AB*	TO-92	TO-243AA**
250V	7.0Ω	2.0V	1.2A	TN5325K1	TN5325N3	TN5325N8

* Same as SOT-23. All units shipped on 3,000 piece carrier tape reels.
** Shipped on 2,000 piece carrier tape and reels.

Product marking for SOT-23:

N3C✳

where ✳ = 2-week alpha date code

Product marking for TO-243AA

TN3C✳

Where ✳ = 2-week alpha date code

Features

- ❑ Low threshold – 2.0V max.
- ❑ Free from secondary breakdown
- ❑ Low power drive requirement
- ❑ Low C_{ISS} and fast switching speeds
- ❑ Excellent thermal stability
- ❑ High input impedance and high gain
- ❑ Complementary N- and P-channel devices

Applications

- ❑ Logic level interfaces – ideal for TTL and CMOS
- ❑ Solid state relays
- ❑ Battery operated systems
- ❑ Photo voltaic drives
- ❑ Analog switches
- ❑ General purpose line drivers
- ❑ Telecom switches

Advanced DMOS Technology

These enhancement-mode (normally-off) transistors utilize a vertical DMOS structure and Supertex's well-proven silicon-gate manufacturing process. This combination produces devices with the power handling capabilities of bipolar transistors and with the high input impedance and positive temperature coefficient inherent in MOS devices. Characteristic of all MOS structures, these devices are free from thermal runaway and thermally-induced secondary breakdown.

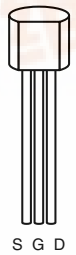
Supertex's vertical DMOS FETs are ideally suited to a wide range of switching and amplifying applications where high breakdown voltage, high input impedance, low input capacitance, and fast switching speeds are desired.

Absolute Maximum Ratings

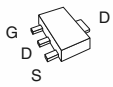
Drain-to-Source Voltage	BV_{DSS}
Drain-to-Gate Voltage	BV_{DGS}
Gate-to-Source Voltage	± 20V
Operating and Storage Temperature	-55°C to +150°C
Soldering Temperature*	300°C

* Distance of 1.6 mm from case for 10 seconds.

Package Options



TO-92



TO-243AA
(SOT-89)

TO-236AB
(SOT-23)

Note: See Package Outline section for dimensions.

11/12/01

Thermal Characteristics

Package	I_D (continuous)*	I_D (pulsed)	Power Dissipation @ T_A = 25°C	θ_{jc} °C/W	θ_{ja} °C/W	I_{DR}*	I_{DRM}
TO-236AB	150mA	400mA	0.36W	200	350	150mA	400mA
TO-92	215mA	800mA	0.74W	125	170	215mA	800mA
TO-243AA	316mA	1.5A	1.6W**	15	78**	316mA	1.5A

* I_D (continuous) is limited by max rated T_j.

**Mounted on FR5 board. 25mm x 25mm x 1.57mm. Significant P_D increase possible on ceramic substrate.

Electrical Characteristics (@ 25°C unless otherwise specified)

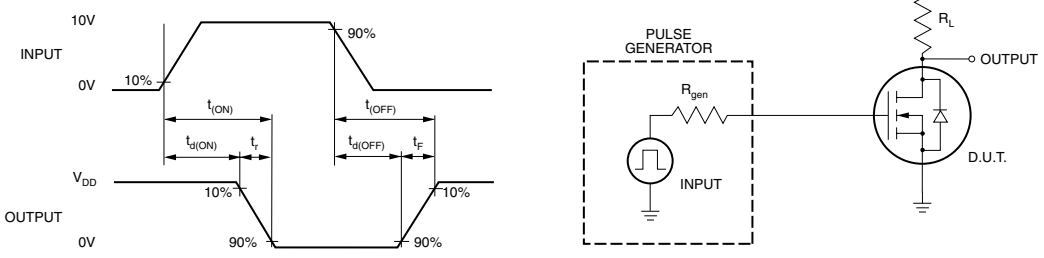
Symbol	Parameter	Min	Typ	Max	Unit	Conditions
BV_{DSS}	Drain-to-Source Breakdown Voltage	250			V	I_D = 100μA, V_{GS} = 0V
$V_{GS(th)}$	Gate Threshold Voltage	0.6		2.0	V	V_{GS} = V_{DS}, I_D = 1mA
$\Delta V_{GS(th)}$	Change in $V_{GS(th)}$ with Temperature			-4.5	mV/°C	I_D = 1mA, V_{GS} = V_{DS}
I_{GSS}	Gate Body Leakage			100	nA	V_{GS} = ±20V, V_{DS} = 0V
I_{DSS}	Zero Gate Voltage Drain Current			1.0	μA	V_{GS} = 0V, V_{DS} = 100V
				10.0	μA	V_{GS} = 0V, V_{DS} = Max Rating
				1.0	mA	V_{GS} = 0V, V_{DS} = 0.8 Max Rating, T_A = 125°C
$I_{D(ON)}$	ON-State Drain Current	0.6			A	V_{GS} = 4.5V, V_{DS} = 25V
		1.2				V_{GS} = 10V, V_{DS} = 25V
$R_{DS(ON)}$	Static Drain-to-Source ON-State Resistance			8.0	Ω	V_{GS} = 4.5V, I_D = 150mA
				7.0	Ω	V_{GS} = 10V, I_D = 1.0A
$\Delta R_{DS(ON)}$	Change in $R_{DS(ON)}$ with Temperature			1.0	%/°C	V_{GS} = 4.5V, I_D = 150mA
G_{FS}	Forward Transconductance	150			m℧	V_{DS} = 25V, I_D = 200mA
C_{ISS}	Input Capacitance			110	pF	V_{GS} = 0V, V_{DS} = 25V, f = 1MHz
C_{OSS}	Common Source Output Capacitance			60		
C_{RSS}	Reverse Transfer Capacitance			23		
$t_{d(ON)}$	Turn-ON Delay Time			20	ns	V_{DD} = 25V, I_D = 150mA, R_{GEN} = 25Ω
t_r	Rise Time			15		
$t_{d(OFF)}$	Turn-OFF Delay Time			25		
t_f	Fall Time			25		
V_{SD}	Diode Forward Voltage Drop			1.8	V	I_{SD} = 200mA, V_{GS} = 0V
t_{rr}	Reverse Recovery Time		300		ns	I_{SD} = 200mA, V_{GS} = 0V

Notes:

1.All D.C. parameters 100% tested at 25°C unless otherwise stated. (Pulse test: 300μs pulse, 2% duty cycle.)

2.All A.C. parameters sample tested.

Switching Waveforms and Test Circuit



Supertex inc
1235 Bordeaux Drive, Sunnyvale, CA 94089